

TRANSPORT PHENOMENA IN THE MAGNETICALLY MODULATED SPINELS: Zn1-xCuxCr2Se4 (WHERE $0.0 \le x \le 1.0$)

T. Gro, H. Duda, J. Warczewski

► To cite this version:

T. Gro , H. Duda, J. Warczewski. TRANSPORT PHENOMENA IN THE MAGNETICALLY MOD-ULATED SPINELS: Zn1-xCuxCr2Se4 (WHERE $0.0 \le x \le 1.0$). Journal de Physique Colloques, 1988, 49 (C8), pp.C8-869-C8-870. 10.1051/jphyscol:19888393 . jpa-00228580

HAL Id: jpa-00228580 https://hal.science/jpa-00228580

Submitted on 4 Feb 2008

HAL is a multi-disciplinary open access archive for the deposit and dissemination of scientific research documents, whether they are published or not. The documents may come from teaching and research institutions in France or abroad, or from public or private research centers. L'archive ouverte pluridisciplinaire **HAL**, est destinée au dépôt et à la diffusion de documents scientifiques de niveau recherche, publiés ou non, émanant des établissements d'enseignement et de recherche français ou étrangers, des laboratoires publics ou privés.

TRANSPORT PHENOMENA IN THE MAGNETICALLY MODULATED SPINELS: $Zn_{1-x}Cu_xCr_2Se_4$ (WHERE $0.0 \le x \le 1.0$)

T. Gron (¹), H. Duda (¹) and J. Warczewski (¹)

Silesian University, Institute of Physics, ul. Uniwersytecka 4, 40007 Katowice, Poland

Abstract. – The spinels under study are p-type semiconductors showing a change of the conductivity character from the conductive into metallic one at $x \sim 0.3$. An increase of the electrical conductivity with the copper concentration in a sample is linked both with the increase of the hole mobility and the hole concentration. For $x \ge 0.05$ partial degeneracy of the semiconductor state is observed.

1. Introduction

The spinels of the series $Zn_{1-x}Cu_xCr_2Se_4$ have been studied since many years because of their extremely interesting magnetic and electrical properties [1-5]. The magnetic phase transitions were observed in these spinels from an antiferromagnetic spiral structure for x = 0 through a conical structure for $0.05 \le x \le$ 0.7 to a ferromagnetic structure for $x \ge 0.8$ [3]. The explanation of these properties was based on the assumption of the mixed valence of chromium $(Cr^{3+},$ Cr^{4+} with the concentration of Cr^{4+} equal to x (i.e. to the copper concentration) [1, 3]. The aim of this paper is the presentation of the experimental results concerning the electrical conductivity and the Seebeck effect in the spinel series $Zn_{1-x}Cu_xCr_2Se_4$ in the whole range of concentrations as well as an attempt to evaluate both the carrier concentration and the mobility and the Fermi energy on the base of the theoretical considerations.

2. Experimental and results

The polycristalline samples of $Zn_{1-x}Cu_xCr_2Se_4$ with x = 0.0, 0.01, 0.02, 0.025, 0.05, 0.07, 0.1, 0.2, 0.3, 0.5, 0.7, 0.8, 0.9 and 1.0 have been studied. The technology and the methods of the measurements of both the electrical conductivity and the Seebeck coefficient are described in [1, 6-8]. From the measurement of the electrical conductivity (σ) and the Seebeck coefficient (α) it follows, that all the spinels under study are p-type semiconductors. The Seebeck coefficient decreases from 451 μ V/K at x = 0 to 17 μ V/K at x = 1. For ZnCr₂Se₄ the Seebeck coefficient increases almost linearly with temperature. For the samples with $x \cong 0.3$ a change of the conductivity character from the semiconductive into metallic one is observed. The curves $\ln \sigma vs. 10^3/T$ reveal bends indicating clearly two values of the activation energy E, which was determined for each straight line part of the curve from the relation $\sigma = \sigma_0 \exp\left(-E/kT\right)$ with the accuracy of ± 0.0005 eV.

3. Calculations

To calculate the concentration p, the mobility μ and the Fermi energy $E_{\rm F}$ a procedure described in [9] was used with the following assumptions: a) the extrinsic conductivity is of one type (p-type); b) the Znvacancies make the acceptor levels (playing role of a double acceptor) [4]; c) there exist two independent acceptor levels with different activation energies (E_1 and E_2). Taking into account the well-known formulae for the hole concentration p in the valence band and for the concentration N_i of the acceptor levels filled doubly as well as assuming electrical neutrality $p = N_i$ a 3rd order equation was obtained:

$$Ay^3 + By^2 + Cy + D = 0 (1)$$

where: $y = \exp\left[-E_{\rm F}/kT\right]$,

A, B, C, D – coefficients which are functions of E_1 , E_2 , N_d and N_s .

The values N_s and N_d , i.e. the concentrations of both the shallow and deep acceptor levels were determined from the condition:

$$\sigma(T) / \sigma(T_0) = p(T) / p(T_0)$$
⁽²⁾

where both p(T) and $p(T_0)$ are functions of either (E_1, N_s) or (E_2, N_d) , according to the corresponding straight line interval of the conductivity curve (ln σ vs. $10^3/\text{T}$) (see Tab. I). Solving the equation (1) with the use of the method described in [10] one comes to the following formulae:

$$p = N_{\rm v} y_1 \tag{3}$$

$$\mu = \sigma/eN_{\mathbf{v}}y_1 \tag{4}$$

$$E_{\rm F} = kT \ln (1/y_1) \tag{5}$$

where: y_1 - the only one positive solution of the equation (1), N_v - effective density of states of the valence band, e - elementary charge, k - Boltzmann constant. The results at 300 K are presented in figure 1. It turns out that: 1) μ strongly increases with temperature for $0.0 \leq x < 0.07$; 2) $\mu(T) = \text{const for } x = 0.07$ and 0.1; 3) μ decreases with the increase of tempera-

Table I. – Values of E_1 , E_2 , N_s and N_d for the spinels under study.

x	E_1 [eV]	E_2 [eV]	$N_{\rm d}~{ m [m^{-3}]}$	$N_{\rm s} \ [{\rm m}^{-3}]$
0.00	0.056	0.2	$1.2 imes 10^{21}$	$2.4 imes 10^{21}$
0.01	0.034	0.1	$1.8 imes 10^{23}$	$1.1 imes 10^{24}$
0.02	0.027	0.086	$2.6 imes10^{23}$	$1.9 imes 10^{24}$
0.025	0.016	0.066	$3.2 imes 10^{23}$	$2.0 imes10^{24}$
0.05	0.0071	0.045	$4.6 imes 10^{23}$	$2.6 imes 10^{24}$
0.07	0.0093	0.044	$7.0 imes10^{23}$	$3.4 imes10^{24}$
0.10	0.0084	0.057	$8.2 imes 10^{23}$	$5.4 imes10^{24}$
0.20	0.0049	0.47	$9.0 imes10^{23}$	$7.2 imes10^{24}$
0.30	0.0033	-0.0004	$4.0 imes 10^{24}$	$1.2 imes 10^{25}$
0.50	0.0049	-0.0241	$1.9 imes 10^{25}$	$7.8 imes10^{25}$
0.70	0.0046	-0.0224	$4.9 imes10^{25}$	$1.7 imes 10^{26}$
0.80	0.0044	-0.0305	$5.2 imes10^{25}$	$2.4 imes10^{26}$
0.90	0.0027	-0.0211	$1.6 imes 10^{26}$	$5.0 imes10^{26}$
1.00	-0.0025	-0.0271	$2.0 imes 10^{26}$	$5.8 imes10^{26}$

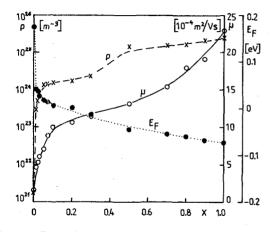


Fig. 1. – Dependence of p, μ and E_F on x at 300 K.

ture for $x \ge 0.2$ and 4) p increases with temperature for all the samples under study, but the smaller x the stronger this dependence.

4. Conclusions

The experimental results and the theoretical considerations suggest, that in the spinel series under study the changes of the electrical conductivity are linked

with both the changes of the concentration and the mobility of the current carriers. It testifies to that the two mechanisms are thermally activated. The increase of the hole concentration p and their mobility μ with the increase of x (see Fig. 1) is connected - as it seems to us – with the increase of Cr^{4+} concentration, which is in the mixed chromium valence band (Cr^{3+}, Cr^{4+}) the main source of the concentration increase of the ptype current carriers. The Zn vacancies influence the hole concentration increase only for ZnCr₂Se₄ and for the samples with small x. The value of $E_{\rm F}$, calculated from equation (5), decreases with the increase of x (see Fig. 1), so that starting from x = 0.05, the inequality $-5 kT < E_{\rm F} < 1 kT$ is valid, which suggests, that these spinels are partially degenerated. This conclusion is confirmed also by the beak dependence of the hole concentration on temperature.

Acknowledgement

This work is partly supported through Project C.P.B. P.01.04.

- Lotgering, F. K., Proc. Int. Conf. Magn., Nottingham (1964) p. 533.
- [2] Okońska-Kozlowska, I. and Krok, J., Z. Anorg. Allg. Chem. 447 (1978) 235.
- [3] Krok, J., Spalek, J., Juszczyk, S. and Warczewski, J., Phys. Rev. B 28 No 11 (1983) 6499.
- [4] Watanabe, T., J. Phys. Soc. Jpn 37 (1974) 140.
- [5] Zhukov, A. A., Kesler, Ya. A., Meshceriakov, V. F. and Rozantsev, A. V., Solid State Phys. 19, No 1 (1984) 3.
- [6] Okońska-Kozlowska, I., Lutz, H. D., Groń, T., Krok, J. and Mydlarz, T., *Mat. Res. Bull.* 19 (1984) 1.
- [7] Groń, T., Gogolowicz, M., Warczewski, J. and Lutz, H. D., J. Phys. 46 (1985) C6-441.
- [8] Groń, T., Kusz, J., Warczewski, J., Ujma, Z. and Okońska-Kozlowska, I., 2 Int. Conf. on Phys. of Magnet. Mater. Sept. 17-22, 1984, Jadwisin (Poland) p. 196; Groń, T., Warczewski, J. and Krok, J., ibid. p. 197.
- [9] Spalek, J., Lubecka, M. and Wegrzyn, A., Phys. Status Solidi B 82 (1977) 107.
- [10] Warmus, M., Zastos. Mat. 6 (1961) 127-135.